

MOS INTEGRATED CIRCUIT $\mu PD16805$

MONOLITHIC H BRIDGE DRIVER CIRCUIT

 μ PD16805 is the monolithic and H bridge driver IC which consists of a CMOS control circuit and a MOS output stage. As compared with the driver of a MOS process using the conventional bipolar transistor, reduction of consumption current and power consumption is possible. With this product, clockwise and the inversion, and the brake function are built in, and it is the best for the drive circuit of the motor for film winding up of a camera, and the motor for auto focus/zooms.

The package has adopted the 16 pin SOP and the 24 pin TSSOP, and corresponds to reduction of mounting area and mounting height. This product corresponds to the drive current to 1.0 A (DC).

FEATURES

· High drive current

I_{D(pulse)} = 4.2 A MAX. at PW ≤ 200 ms (single pulse)

 $I_{D(DC)} = 1.0 A (DC)$

• Low-ON resistance (sum of the upper and lower sides MOS FET)

Ron = 0.4Ω TYP. at ID = 1.0 A

- Standby function that turns OFF charge pump circuit
- · Compact surface mount package

16-pin plastic SOP (1.27 mm pitch)

24-pin plastic TSSOP (0.5 mm pitch)

ORDERING INFORMATION

Part Number	Package
μPD16805GS	16-pin plastic SOP (7.64 mm (300))
μPD16805MA-6A5	24-pin plastic TSSOP (5.72 mm (225))

The information in this document is subject to change without notice.



ABSOLUTE MAXIMUM RATINGS

(TA = 25°C, Glass epoxy substrate 100 mm × 100 mm × 1 mm, 15% copper foil)

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Parameter	Symbol	Conditions	Rating	Unit
O	V _{DD}	Control section	-0.5 to +6.5/+8.0 ^{Note}	V
Supply voltage	VM	Motor section	-0.5 to +6.5/+8.0 ^{Note}	V
V _G pin applied voltage	VG		15	V
Input voltage	VIN		−0.5 to V _{DD} +0.5	V
H bridge drive current	I _{D(DC)}	DC	1.0	Α
H bridge drive current	ID(pulse)	PW ≤ 200 ms (single pulse)	4.2	A/ch
Dower consumption	Рт	GS	1.0	W
Power consumption		MA-6A5	0.7	W
Peak junction temperature	T _{CH(MAX)}		150	°C
Storage temperature	T _{stg}		-55 to +150	°C

Note When the charge pump is used/when VG power-source supply from the exterior.

RECOMMENDED OPERATING CONDITIONS

(TA = 25°C, Glass epoxy substrate 100 mm × 100 mm × 1 mm, 15% copper foil)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
	M	During normal operation	3.0			.,
Supply voltage	V _{DD}	All input pins are low	2.5		6.0/7.5 ^{Note 2}	V
	Vм		0.5			V
Charge pump capacitance	C ₁ to C ₃			0.01		μ F
V _G pin applied voltage ^{Note 1}	V G	At the time of external input	11		14	V
Operating temperature	Та	Ambient temperature	-30		60	°C

Notes 1. When voltage is impressed to VG terminal from the exterior

2. When the charge pump is used/when VG power-source supply from the exterior.

ELECTRICAL SPECIFICATIONS

(Unless otherwise specified, V_{DD} = recommended operating condition, V_M = 0.5 to 6.0 V)

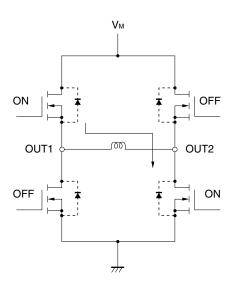
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
V	I _{DD1}	V _{DD} = 5 V, T _A = Recommended conditions Control pins at high level		0.6	2.0	mA
V _{DD} pin current	I _{DD2}	V _{DD} = 5 V, T _A = Recommended conditions Control pins at low level		0.3	10	μΑ
Vм pin current	Ім1	T _A = Reommended conditions Control pins at low level		0.1	10	μΑ
	I м2	Control pins at low level			1.0	μΑ
H bridge ON resistance	Ron	I _D = 1 A, V _{DD} = V _M = 5 V C ₁ = C ₂ = C ₃ = 0.01 μ F sum of the upper and lower sides MOSFET		0.4	0.6	Ω
High-level input voltage	ViH	T _A = Recommended conditions	$0.6 \times V_{DD}$			V
Low-level input voltage	VIL	T _A = Recommended conditions			$0.2 \times V_{\text{DD}}$	V
Charge pump circuit turn-ON time	tong	$V_{DD} = V_M = 5 V$,		0.5	1.0	ms
H bridge output circuit turn-ON time	tоин	T_A = Recommended conditions $C_1 = C_2 = C_3 = 0.01 \mu F$			10	μs
H bridge output circuit turn-OFF time	tоffн	lo = 1 A			5.0	μs
Control pip input pull down register			35	50	65	kΩ
Control pin input pull-down resistor	RIND	T _A = Recommended conditions	25		75	kΩ



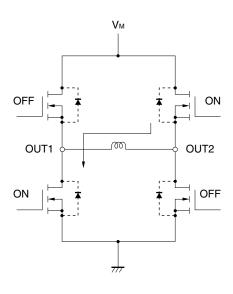
FUNCTION TABLE

	Input	Signal	Funation	
IN1	IN2	INC	STB	Function
Н	Н	Н	Н	Brake mode
Н	L	Н	Н	Forward mode
L	Н	Н	Н	Reverse mode
L	L	Н	Н	Stop mode
Х	Х	L	Н	Stop mode
Х	Х	Х	L	Standby mode

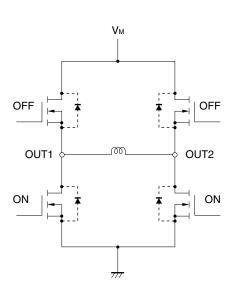




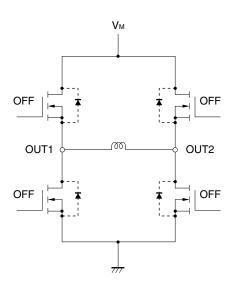
Reverse mode



Brake mode



Stop mode

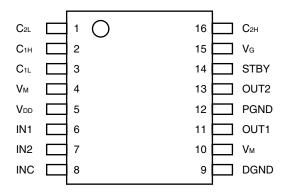




Terminal function

• μPD16805GS

Package: 16 pin plastic SOP



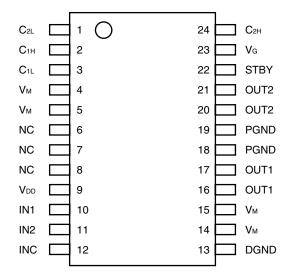
Terminal No.	Terminal name	Terminal function
1	C ₂ L	The capacitor connection terminal for charge pumps
2	С1н	The capacitor connection terminal for charge pumps
3	C ₁ L	The capacitor connection terminal for charge pumps
4	Vм	Motor block supply voltage input terminal
5	V _{DD}	Control block supply voltage input terminal
6	IN1	Input terminal
7	IN2	Input terminal
8	INC	Input terminal
9	DGND	Control block GND terminal
10	Vм	Motor block supply voltage input terminal
11	OUT1	Output terminal
12	PGND	Output block GND terminal
13	OUT2	Output terminal
14	STBY	Standby terminal
15	V _G	Gate input terminal
16	С2н	The capacitor connection terminal for charge pumps



Terminal function

• μPD16805MA-6A5

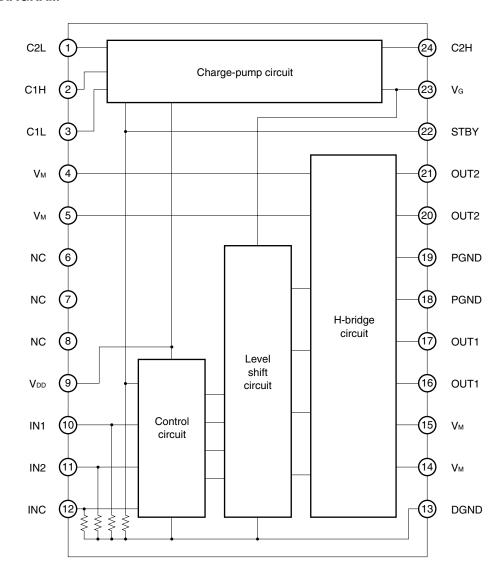
Package: 24 pin plastic TSSOP



Terminal No.	Terminal name	Terminal function
1	C ₂ L	The capacitor connection terminal for charge pumps
2	С1н	The capacitor connection terminal for charge pumps
3	C ₁ L	The capacitor connection terminal for charge pumps
4	Vм	Motor block supply voltage input terminal
5	V _M	Motor block supply voltage input terminal
6	NC	no used terminal
7	NC	no used terminal
8	NC	no used terminal
9	V _{DD}	Control block supply voltage input terminal
10	IN1	Input terminal
11	IN2	Input terminal
12	INC	Input terminal
13	DGND	Control block GND terminal
14	Vм	Motor block supply voltage input terminal
15	Vм	Motor block supply voltage input terminal
16	OUT1	Output terminal
17	OUT1	Output terminal
18	PGND	Output block GND terminal
19	PGND	Output block GND terminal
20	OUT2	Output terminal
21	OUT2	Output terminal
22	STBY	Standby terminal
23	V _G	Gate input terminal
24	С2н	The capacitor connection terminal for charge pumps

Notice Please connect all the terminals that have plural. (V_M, OUT1, OUT2, PGND) No used terminals are connected to ground.

BLOCK DIAGRAM

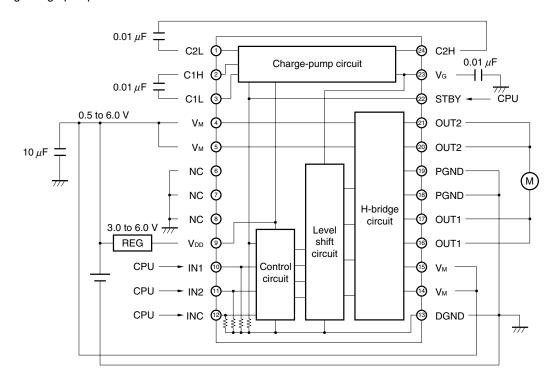


The connection diagram of μ PD16805MA-6A5 shows the block diagram. It of μ PD16805GS does not change, except that there are not NC and plural terminals. The plural terminal should connect all terminals.

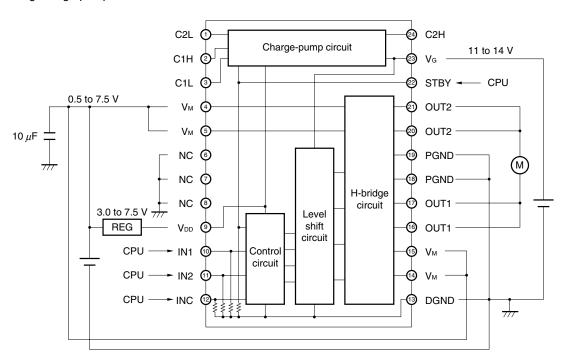


The example of standard connection

(1) using charge pump circuit



(2) unusing charge pump circuit



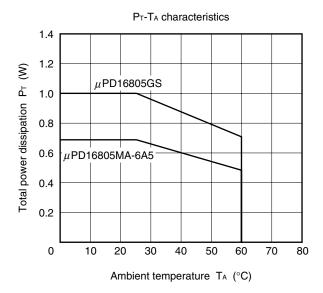
The connection diagram of μ PD16805MA-6A5 is shown by the inside of a figure.

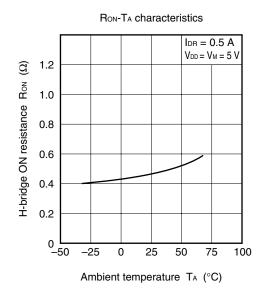
This circuit diagrams are an example of connection, and are not intended for use in actual design-ins.

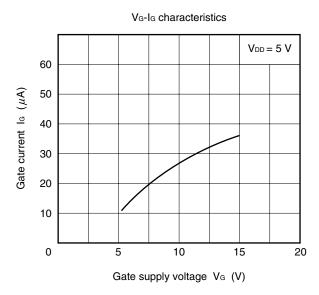
Moreover, it recommendeds inserting an about several μF capacitor between VM-GND for surge voltage protection of the output stage.

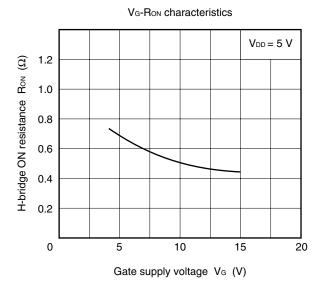


TYPICAL CHARACTERISTICS (TA = 25°C)





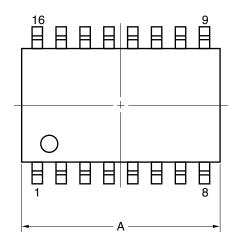




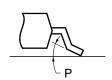


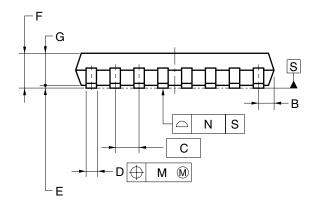
PACKAGE DIMENSION (µPD16805GS)

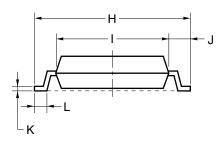
16-PIN PLASTIC SOP (7.62 mm (300))



detail of lead end







NOTE

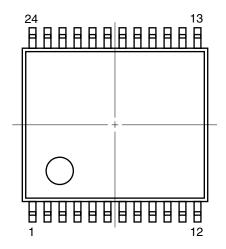
Each lead centerline is located within 0.12 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
Α	10.2±0.2
В	0.78 MAX.
С	1.27 (T.P.)
D	$0.42^{+0.08}_{-0.07}$
Е	0.1±0.1
F	1.65±0.15
G	1.55
Н	7.7±0.3
- 1	5.6±0.2
J	1.1±0.2
K	$0.22^{+0.08}_{-0.07}$
L	0.6±0.2
М	0.12
N	0.10
Р	3°+7°

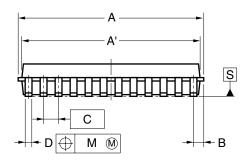
P16GM-50-300B-6

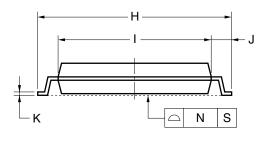
PACKAGE DIMENSION (µPD16805MA-6A5)

24-PIN PLASTIC TSSOP (5.72 mm (225))



detail of lead end





NOTE

Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
Α	6.65±0.10
A'	6.5±0.1
В	0.575
С	0.5 (T.P.)
D	0.22±0.05
Е	0.1±0.05
F	1.2 MAX.
G	1.0±0.05
Н	6.4±0.1
I	4.4±0.1
J	1.0±0.1
K	0.17±0.025
L	0.5
М	0.10
N	0.08
Р	3°+5°
R	0.25
S	0.6±0.15
	P24MA-50-6A5



RECOMMENDED SOLDERING CONDITIONS

It is recommended to solder this under the conditions described below.

For soldering methods and conditions other than those listed below, consult NEC.

For details of the recommended soldering conditions, refer to information document "Semiconductor Device Mounting Technology Manual".

μ PD16805GS

Soldering Method	Soldering Conditions	Recommended Conditions Symbol
Infrared reflow	Peak package temperature: 235°C, Time: 30 seconds MAX. (210°C MIN.), Number of times: 2 MAX.	IR35-00-2
VPS	Peak package temperature: 215°C, Time: 40 seconds MAX. (200°C MIN.), Number of times: 2 MAX.	VP15-00-2

The number of storage days at 25°C, 65% RH after the dry pack has been opened

μPD16805MA-6A5

Soldering Method	Soldering Conditions	Recommended Conditions Symbol
Infrared reflow	Package peak temperature: 235°C; Duration: 30 sec. max. (210°C or above): Number of times: Max. 3; Time limit: None ^{Note} Flux: Rosin type flux with reduced chlorine content (chlorine 0.2 Wt% or less) is recommended.	IR35-00-3
VPS	Package peak temperature: 215°C; Duration: 40 sec. max. (200°C or above): Number of times:3; Time limit: None ^{Note} Flux: Rosin type flux with reduced chlorine content (chlorine 0.2 Wt% or less) is recommended.	VP15-00-3
Wave soldering	Package peak temperature: 260°C or less, Duration: 10 sec. Max.,. Preparatory heating temperature: 120°C or less; Number of times: 1 Flux: Rosin type flux with reduced chlorine content (chlorine 0.2 Wt% or less) is recommended.	WS60-00-1

Note The number of storage days at 25°C, 65% RH after the dry pack has been opened

Caution Use of more than one soldering method should be avoided.

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[MEMO]



[MEMO]

[MEMO]



NOTES FOR CMOS DEVICES -

1) PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

(3) STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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